



POWER-MOS FET

FIELD EFFECT POWER TRANSISTOR

IRFD112,113

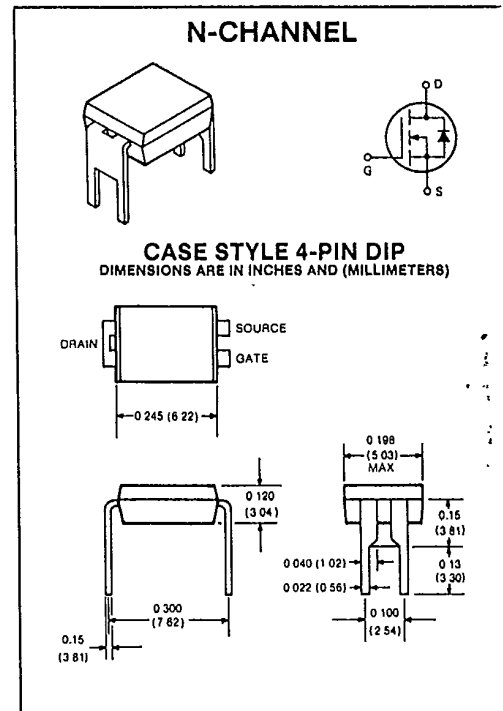
0.8 AMPERES
100, 60 VOLTS
 $R_{DS(ON)} = 0.8 \Omega$

This series of N-Channel Enhancement-mode Power MOSFETs utilizes GE's advanced Power DMOS technology to achieve low on-resistance with excellent device ruggedness and reliability.

This design has been optimized to give superior performance in most switching applications including: switching power supplies, inverters, converters and solenoid/relay drivers. Also, the extended safe operating area with good linear transfer characteristics makes it well suited for many linear applications such as audio amplifiers and servo motors.

Features

- Polysilicon gate — Improved stability and reliability
- No secondary breakdown — Excellent ruggedness
- Ultra-fast switching — Independent of temperature
- Voltage controlled — High transconductance
- Low input capacitance — Reduced drive requirement
- Excellent thermal stability — Ease of paralleling



maximum ratings ($T_A = 25^\circ\text{C}$) (unless otherwise specified)

RATING	SYMBOL	IRFD112	IRFD113	UNITS
Drain-Source Voltage	V_{DSS}	100	60	Volts
Drain-Gate Voltage, $R_{GS} = 1M\Omega$	V_{DGR}	100	60	Volts
Continuous Drain Current @ $T_A = 25^\circ\text{C}^{(1)}$ @ $T_A = 100^\circ\text{C}^{(1)}$	I_D	0.80 0.54	0.80 0.54	A A
Pulsed Drain Current ⁽²⁾	I_{DM}	6.4	6.4	A
Gate-Source Voltage	V_{GS}	± 20	± 20	Volts
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	1.2 9.6	1.2 9.6	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ\text{C}$

thermal characteristics

Thermal Resistance, Junction to Ambient ⁽¹⁾	$R_{\theta JA}$	105	105	$^\circ\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes: $\frac{1}{8}$ " from Case for 5 Seconds	T_L	300	300	$^\circ\text{C}$

(1) Device mounted to vertical pc board in free air with drain lead soldered to 0.20 in² minimum copper run area.

(2) Repetitive Rating: Pulse width limited by max. junction temperature.

electrical characteristics ($T_A = 25^\circ\text{C}$) (unless otherwise specified)

CHARACTERISTIC	SYMBOL	MIN	TYP	MAX	UNIT
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off characteristics

Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250 \mu A$)	IRFD112 IRFD113	BV _{DSS}	100 60	— —	— —	Volts
Zero Gate Voltage Drain Current ($V_{DS} = \text{Max Rating}, V_{GS} = 0V, T_A = 25^\circ\text{C}$) ($V_{DS} = \text{Max Rating}, \times 0.8, V_{GS} = 0V, T_A = 125^\circ\text{C}$)		I _{DSS}	— —	— —	250 1000	μA
Gate-Source Leakage Current ($V_{GS} = \pm 20V$)		I _{GSS}	—	—	± 500	nA

on characteristics*

Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 250 \mu A$)	$T_A = 25^\circ\text{C}$	V _{GS(TH)}	2.0	—	4.0	Volts
On-State Drain Current ($V_{GS} = 10V, V_{DS} = 10V$)		I _{D(ON)}	0.8	—	—	A
Static Drain-Source On-State Resistance ($V_{GS} = 10V, I_D = 0.8A$)		R _{DS(ON)}	—	0.60	0.80	Ohms
Forward Transconductance ($V_{DS} = 10V, I_D = 0.8A$)		g _{fs}	0.56	0.75	—	mhos

dynamic characteristics

Input Capacitance	V _{GS} = 0V	C _{iss}	—	145	200	pF
Output Capacitance	V _{DS} = 25V	C _{oss}	—	65	100	pF
Reverse Transfer Capacitance	f = 1 MHz	C _{rss}	—	20	25	pF

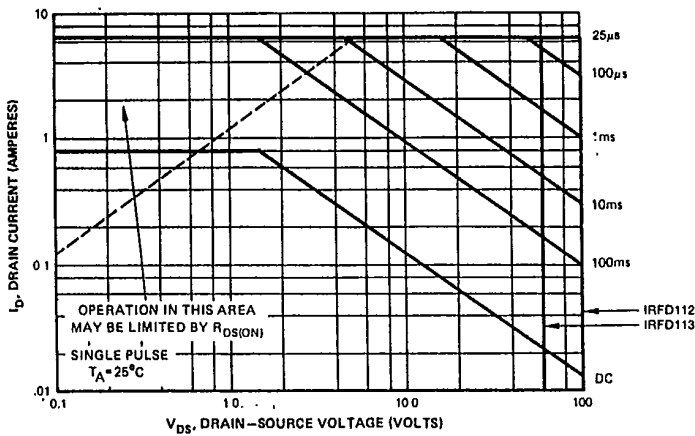
switching characteristics*

Turn-on Delay Time	V _{DS} = 30V	t _{d(on)}	—	15	—	ns
Rise Time	I _D = 0.8A, V _{GS} = 15V	t _r	—	15	—	ns
Turn-off Delay Time	R _{GEN} = 50 Ω , R _{GS} = 12.5 Ω	t _{d(off)}	—	30	—	ns
Fall Time	(R _{GS} (EQUIV.) = 10 Ω)	t _f	—	10	—	ns

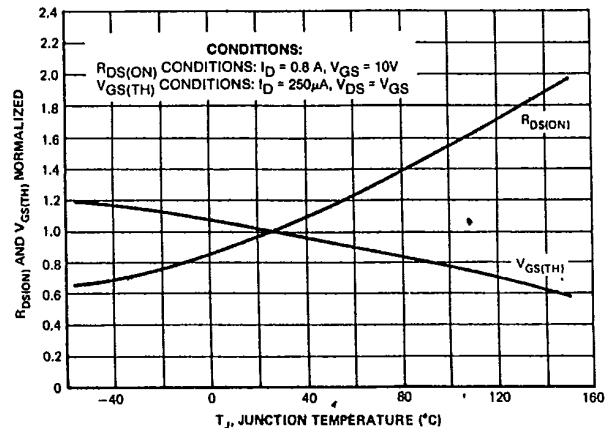
source-drain diode ratings and characteristics*

Continuous Source Current	I _S	—	—	0.8	A
Pulsed Source Current	I _{SM}	—	—	6.4	A
Diode Forward Voltage ($T_A = 25^\circ\text{C}, V_{GS} = 0V, I_S = 0.8A$)	V _{SD}	—	0.8	2.0	Volts
Reverse Recovery Time ($I_S = 1.0A, di_s/dt = 100A/\mu s, T_A = 125^\circ\text{C}$)	t _{rr} Q _{RR}	—	90 0.2	—	ns μC

*Pulse Test: Pulse width $\leq 300 \mu s$, duty cycle $\leq 2\%$



MAXIMUM SAFE OPERATING AREA



TYPICAL NORMALIZED R_{DS(ON)} AND V_{GS(TH)} VS. TEMP.